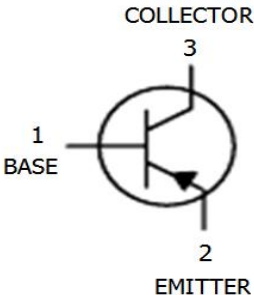
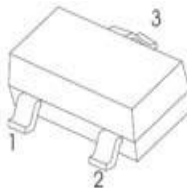


TRANSI STOR (PNP)	SOT-23 Plastic-Encapsulate Transistors																																				
<u>SOT-23</u>  1.BASE 2.EMITTER 3.COLLECTOR Marking :BA	Features ※ Power Dissipation																																				
MAXIMUM RATINGS (Ta=25℃ unless otherwise noted) <table><tr><th>Parameter</th><th>Symbol</th><th>Value</th><th>Unit</th></tr><tr><td>Collector-Base Voltage</td><td>VCBO</td><td>-50</td><td>V</td></tr><tr><td>Collector-Emitter Voltage</td><td>VCEO</td><td>-50</td><td>V</td></tr><tr><td>Emitter-Base Voltage</td><td>VEBO</td><td>-5</td><td>V</td></tr><tr><td>Collector Current</td><td>IC</td><td>-150</td><td>mA</td></tr><tr><td>Collector Power Dissipation</td><td>PC</td><td>400</td><td>mW</td></tr><tr><td>Thermal Resistance From Junction To Ambient</td><td>RΘJA</td><td>312</td><td>℃/W</td></tr><tr><td>Junction Temperature</td><td>Tj</td><td>150</td><td>℃</td></tr><tr><td>Storage Temperature</td><td>Tstg</td><td>-55~+150</td><td>℃</td></tr></table>		Parameter	Symbol	Value	Unit	Collector-Base Voltage	VCBO	-50	V	Collector-Emitter Voltage	VCEO	-50	V	Emitter-Base Voltage	VEBO	-5	V	Collector Current	IC	-150	mA	Collector Power Dissipation	PC	400	mW	Thermal Resistance From Junction To Ambient	RΘJA	312	℃/W	Junction Temperature	Tj	150	℃	Storage Temperature	Tstg	-55~+150	℃
Parameter	Symbol	Value	Unit																																		
Collector-Base Voltage	VCBO	-50	V																																		
Collector-Emitter Voltage	VCEO	-50	V																																		
Emitter-Base Voltage	VEBO	-5	V																																		
Collector Current	IC	-150	mA																																		
Collector Power Dissipation	PC	400	mW																																		
Thermal Resistance From Junction To Ambient	RΘJA	312	℃/W																																		
Junction Temperature	Tj	150	℃																																		
Storage Temperature	Tstg	-55~+150	℃																																		

ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Collector-base breakdown voltage	V(BR)CBO	IC= -100 μ A, IE=0	-50			V
Collector-emitter breakdown voltage	V(BR)CEO	IC= -0.1mA, IB=0	-50			V
Emitter-base breakdown voltage	V(BR)EBO	IE=-100 μ A, IC=0	-5			V
Collector cut-off current	ICBO	VCB=-50 V, IE=0			-0.1	μ A
Collector cut-off current	ICEO	VCB=-50V, IE=0			-0.1	μ A
Emitter cut-off current	IEBO	VEB= -5V, IC=0			-0.1	μ A
DC current gain	hFE	VCE=-6V, IC= -2mA	100		700	
	hFE	VCE=-6V, IC= -0.2mA	70			
Collector-emitter saturation voltage	VCE(sat)	IC=-100 mA, IB= -10mA			-0.3	V
Base-emitter saturation voltage	VBE(sat)	IC=-100 mA, IB= -10mA			-1.1	V
Transition frequency	fT	VCE=-10V, IC= -1mA f=30MHz	80			MHz
Collector Output Capacitance	Cob	VCB=-10V, IE= 0 f=1MHz			7	pf
Noise Figure	NF	VCE=-6V, IC= -0.1mA Rg=10k Ω ; f=1kHz			6	dB

CLASSIFICATION OF hFI

Rank	O	Y	GR	BL
Range	70-140	120-240	200-400	350-700

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

